



MPF02N65

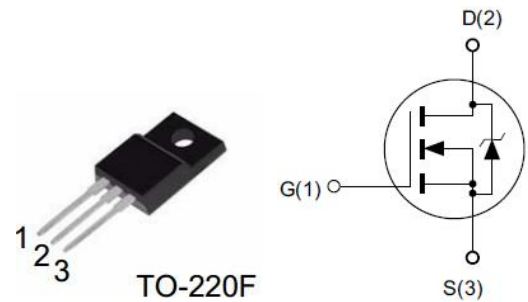
N-Channel Power MOSFET

Features

- ◆ 650V, 2A, $R_{DS(ON)}(Typ.) = 4.0\Omega @ V_{GS} = 10V$.
- ◆ Low C_{rss}
- ◆ Fast Switching
- ◆ 100% Avalanche Tested

Application

- ◆ Charger
- ◆ Standby Power
- ◆ LED Driver



Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Limit	Unit
		TO-220F	
V_{DS}	Drain-Source Voltage ^a	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_C = 25^\circ C$	2	A
	Drain Current-Continuous, $T_C = 100^\circ C$	1.3	A
I_{DM}	Drain Current-Pulsed ^b	8	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ C$	27	W
E_{AS}	Single Pulsed Avalanche Energy ^d	80	mJ
T_J, T_{STG}	Operating and Store Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	4.63	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max.	100	$^\circ C/W$

Electrical Characteristics $T_J = 25^\circ C$ unless otherwise noted.

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



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■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS} = 10V, I_D = 1A$	-	4.0	5.2	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Ciss	Input Capacitance	$V_{DS} = 25V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	335	-	pF
Coss	Output Capacitance		-	33.2	-	pF
Crss	Reverse Transfer Capacitance		-	3.1	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 325V, I_D = 2A,$ $R_G = 10\Omega, V_{GS} = 10V$	-	11.1	-	ns
t_r	Turn-On Rise Time		-	13.2	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	28.9	-	ns
t_f	Turn-Off Fall Time		-	12.1	-	ns
Qg	Total Gate Charge	$V_{DS} = 520V, I_D = 2A,$ $V_{GS} = 10V$	-	9.5	-	nC
Qgs	Gate-Source Charge		-	1.5	-	nC
Qgd	Gate-Drain Charge		-	4.9	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	2	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	8	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 2A$	-	-	1.5	V
T_{rr}	Body Diode Reverse Recovery Time	$di/dt = 100A/\mu s$ $I_F = 2A, V_{GS} = 0V$	-	218	-	ns
Q_{rr}	Reverse Recovery Charge		-	746	-	nC

Notes:

- $T_J = +25^\circ C$ to $+150^\circ C$.
- Repetitive rating; pulse width limited by maximum junction temperature.
- Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- $L = 10mH, V_{DD} = 50V, I_{as} = 4A, R_G = 25\Omega$ Starting $T_J = 25^\circ C$.

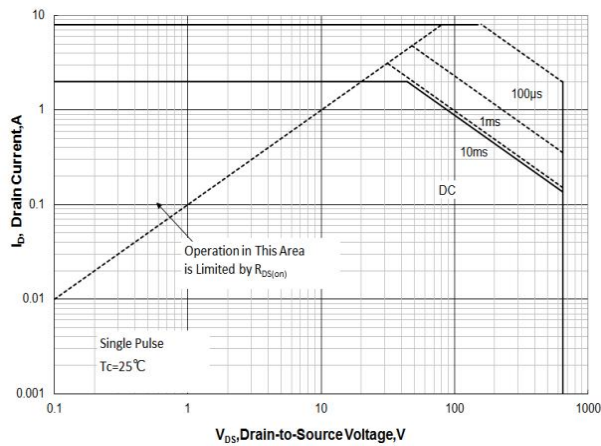


Figure1. Maximum Safe Operating Area

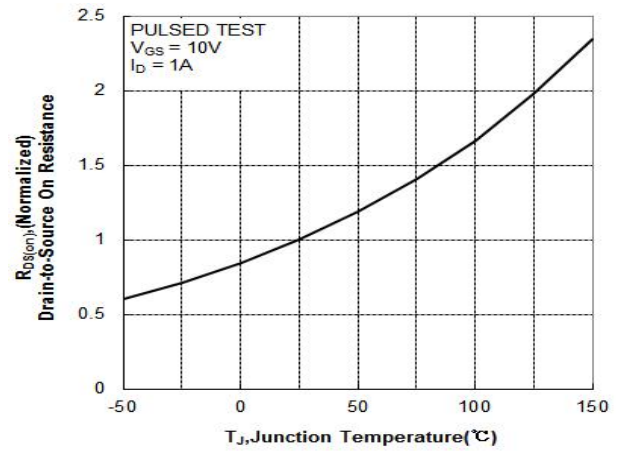


Figure 2. Normalized On-Resistance Variation with Temperature

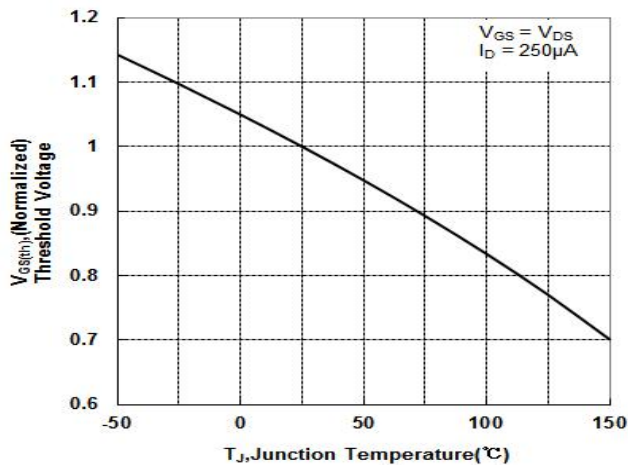


Figure 3. Typical Theshold Voltage vs Junction Temperature

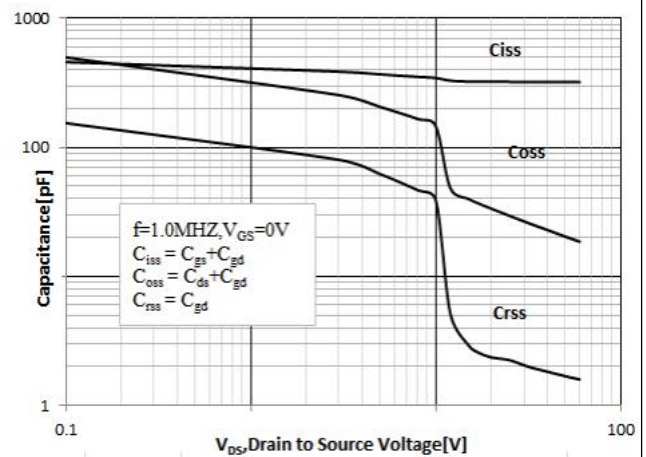


Figure 4. Capacitance Characteristics

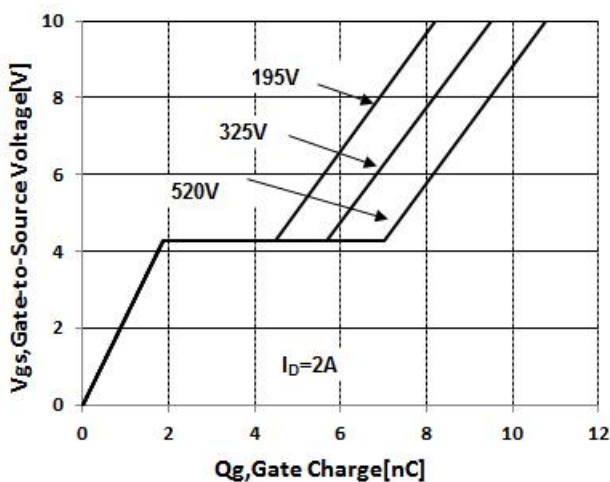


Figure 5. Gate Charge Characteristics

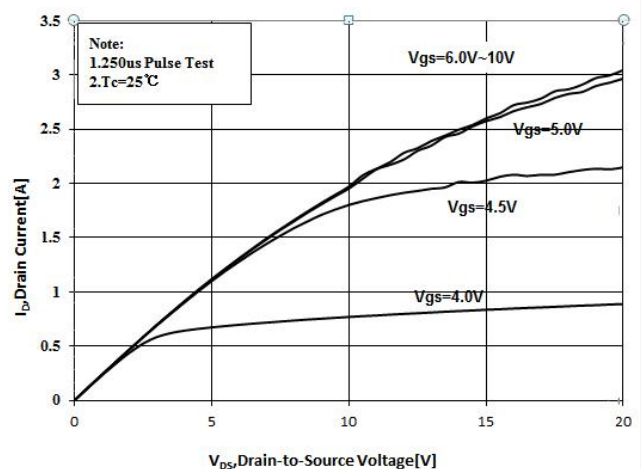


Figure 6. On-State Characteristics

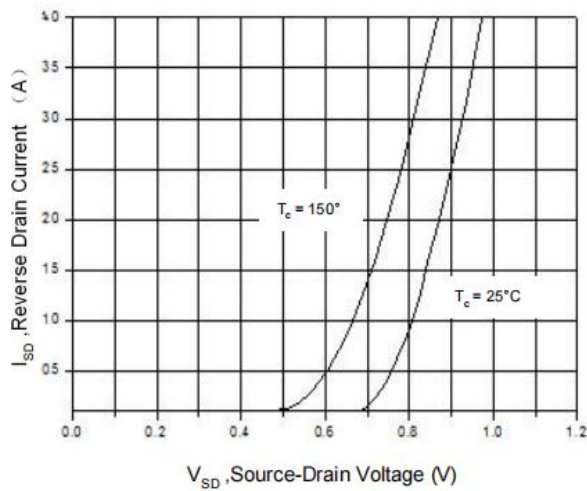


Figure 7. Body Diode Transfer Characteristics

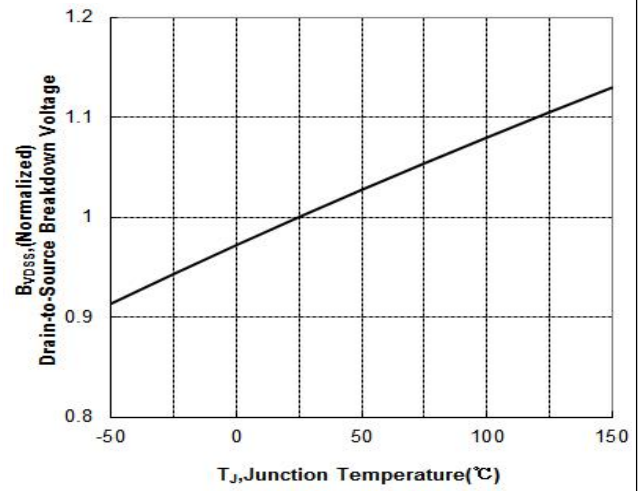


Figure 8. Breakdown Voltage vs Junction Temperature

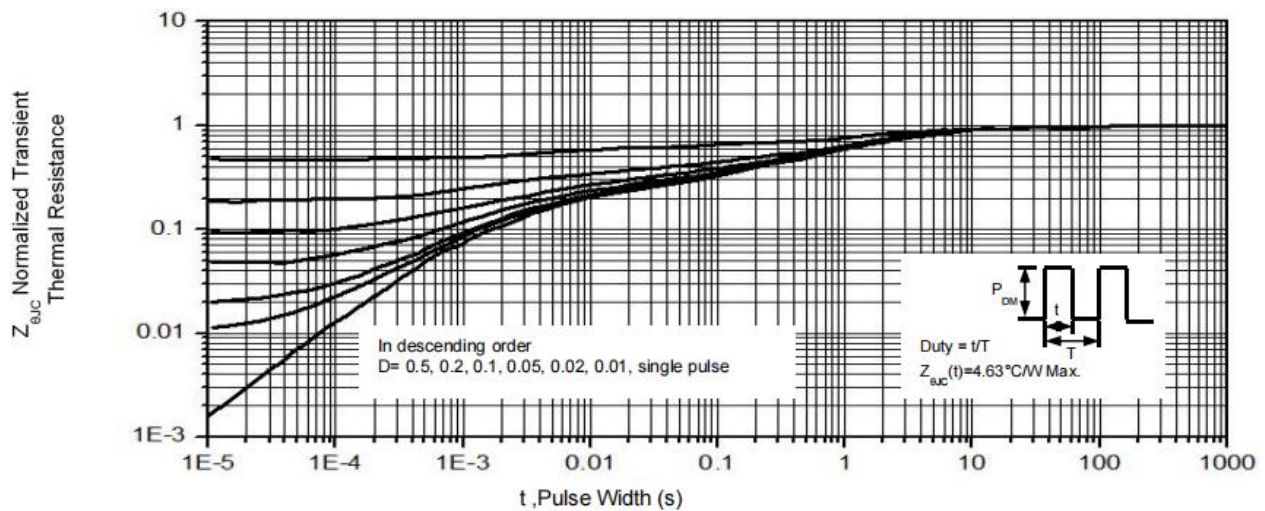


Figure 9. Normalized Effective Transient Thermal Impedance With Pulse Duration

■ Package Information

